

**GaAs SPDT High Isolation Terminated Switch**  
0.5 - 2.0 GHz

SW-394  
V5

**Features**

- Terminated RF Output
- High Isolation: 35 dB up to 2 GHz
- Positive Control
- Nanosecond Switching Speed
- CMOS Compatible Logic
- SOIC-8 Plastic Package

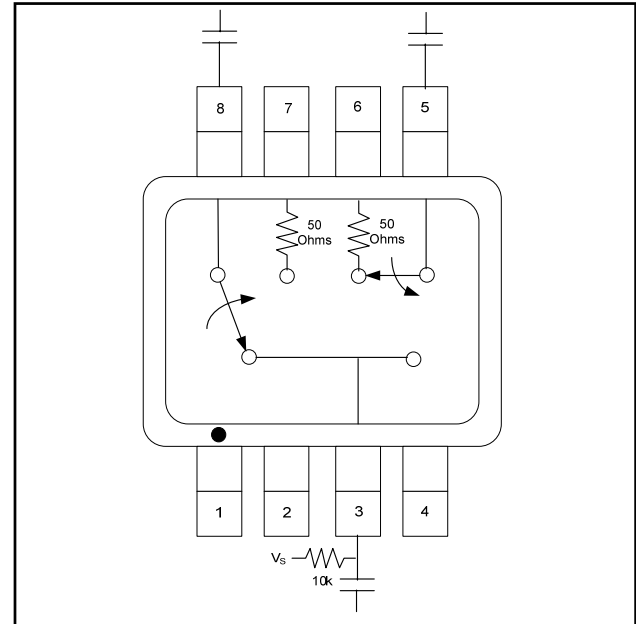
**Description**

M/A-COM's SW-394 is a GaAs monolithic SPDT terminated switch in a low cost SOIC 8-lead plastic package. The SW-394 is ideally suited for use where low power consumption and high isolation are required.

Typical applications include transmit/receive switching, switch matrices and switched filter banks in systems such as radio and cellular equipment.

The SW-394 is fabricated using a mature 1-micron gate length GaAs MESFET process. The process features full chip passivation for increased performance and reliability.

**Functional Schematic**



**Pin Configuration <sup>4</sup>**

Pin No.	Function	Pin No.	Function
1	B	5	RF1
2	GND	6	GND
3	RFC	7	GND
4	A	8	RF2

4. Blocking capacitors are required on all RF ports.  $V_S$  can be applied at any RF port using 10K or greater pull-up resistor.

**Ordering Information <sup>1</sup>**

Part Number	Package
SW-394-PIN	Bulk Packaging
SW-394TR	1000 piece reel
SW-394SMB	Sample Board

1. Reference Application Note M513 for reel size information.

**Absolute Maximum Ratings <sup>2,3</sup>**

Parameter	Absolute Maximum
Input Power	+34 dBm
Operating Voltage ( $V_S, V_A, V_B$ )	+8.5 Volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.

**Truth Table <sup>5,6,7</sup>**

Control Input A	Control Input B	RFC-RF2	RFC-RF1
0	1	Off	On
1	0	On	Off

- 0 = 0 ± 0.2 VDC
- 1 = +5 ± 0.2 VDC,
- $V_S$  = +5 ± 0.2 VDC, 25 µA Max. Current Total

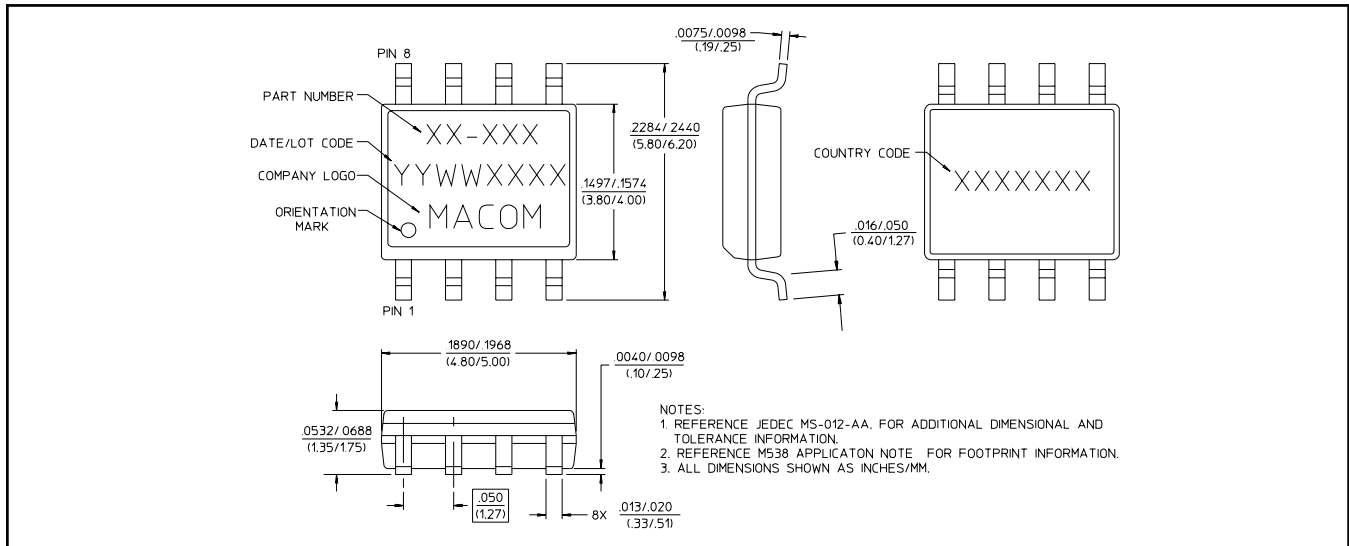
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**Electrical Specifications:  $T_A = 25^\circ\text{C}$**

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Insertion Loss	0.5 - 1.0 GHz	dB	—	1.3	1.5
	1.0 - 2.0 GHz	dB	—	1.4	1.6
Isolation	0.5 - 1.0 GHz	dB	37	40	—
	1.0 - 2.0 GHz	dB	32	35	—
VSWR	0.5 - 1.5 GHz	Ratio	—	1.6:1	—
1 dB Compression	Input Power, +5 V Control/Supply				
	0.5 GHz	dBm	—	24	—
	0.9 GHz	dBm	—	24	—
	1.5 GHz	dBm	—	25	—
Trise, Tfall	10% to 90% RF, 90% to 10% RF	ns	—	34	—
Ton, Toff	50% Control to 90% RF, 50% Control to 10% RF	ns	—	36	—
Transients	In-Band	mV	—	22	—
Input $IP_2$	2-Tone, 5 MHz spacing, +10 dBm each				
	0.5 GHz	dBm	—	67	—
	0.9 GHz	dBm	—	72	—
Input $IP_3$	2-Tone, 5 MHz spacing, +10 dBm each				
	0.5 GHz	dBm	—	47	—
	0.9 GHz	dBm	—	47	—
Control Current	—	$\mu\text{A}$	—	10	25

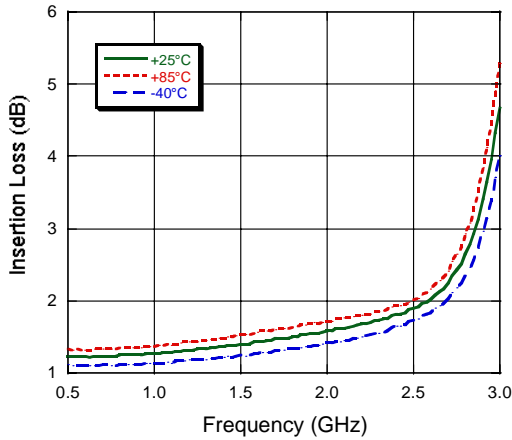
**SOIC-8<sup>†</sup>**



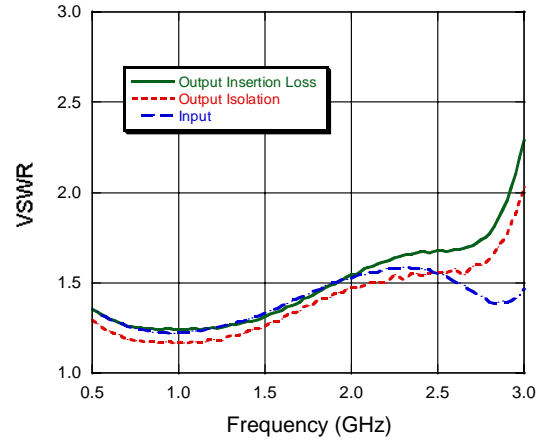
<sup>†</sup>Meets JEDEC moisture sensitivity level 1 requirements.

**Typical Performance Curves**

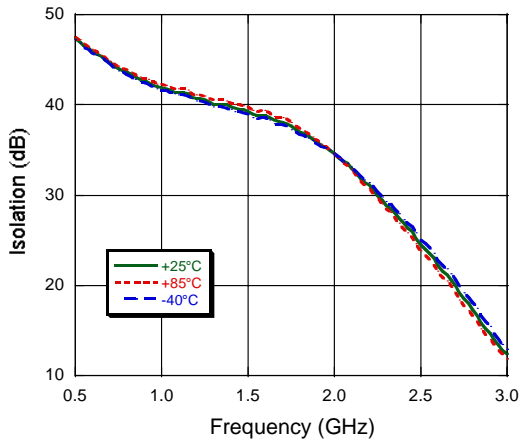
*Insertion Loss vs. Frequency*



*VSWR vs. Frequency*



*Isolation vs. Frequency*



**Handling Procedures**

Please observe the following precautions to avoid damage:

**Static Sensitivity**

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.